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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 14x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l152cct6

2 Description

The ultra-low-power STM32L151xC and STM32L152xC devices incorporate the connectivity power of the universal serial bus (USB) with the high-performance ARM® Cortex®-M3 32-bit RISC core operating at a frequency of 32 MHz (33.3 DMIPS), a memory protection unit (MPU), high-speed embedded memories (Flash memory up to 256 Kbytes and RAM up to 32 Kbytes) and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The STM32L151xC and STM32L152xC devices offer two operational amplifiers, one 12-bit ADC, two DACs, two ultra-low-power comparators, one general-purpose 32-bit timer, six general-purpose 16-bit timers and two basic timers, which can be used as time bases.

Moreover, the STM32L151xC and STM32L152xC devices contain standard and advanced communication interfaces: up to two I2Cs, three SPIs, two I2S, three USARTs and an USB. The STM32L151xC and STM32L152xC devices offer up to 23 capacitive sensing channels to simply add a touch sensing functionality to any application.

They also include a real-time clock and a set of backup registers that remain powered in Standby mode.

Finally, the integrated LCD controller (except STM32L151xC devices) has a built-in LCD voltage generator that allows to drive up to 8 multiplexed LCDs with the contrast independent of the supply voltage.

The ultra-low-power STM32L151xC and STM32L152xC devices operate from a 1.8 to 3.6 V power supply (down to 1.65 V at power down) with BOR and from a 1.65 to 3.6 V power supply without BOR option. They are available in the -40 to +85 °C and -40 to +105 °C temperature ranges. A comprehensive set of power-saving modes allows the design of low-power applications.

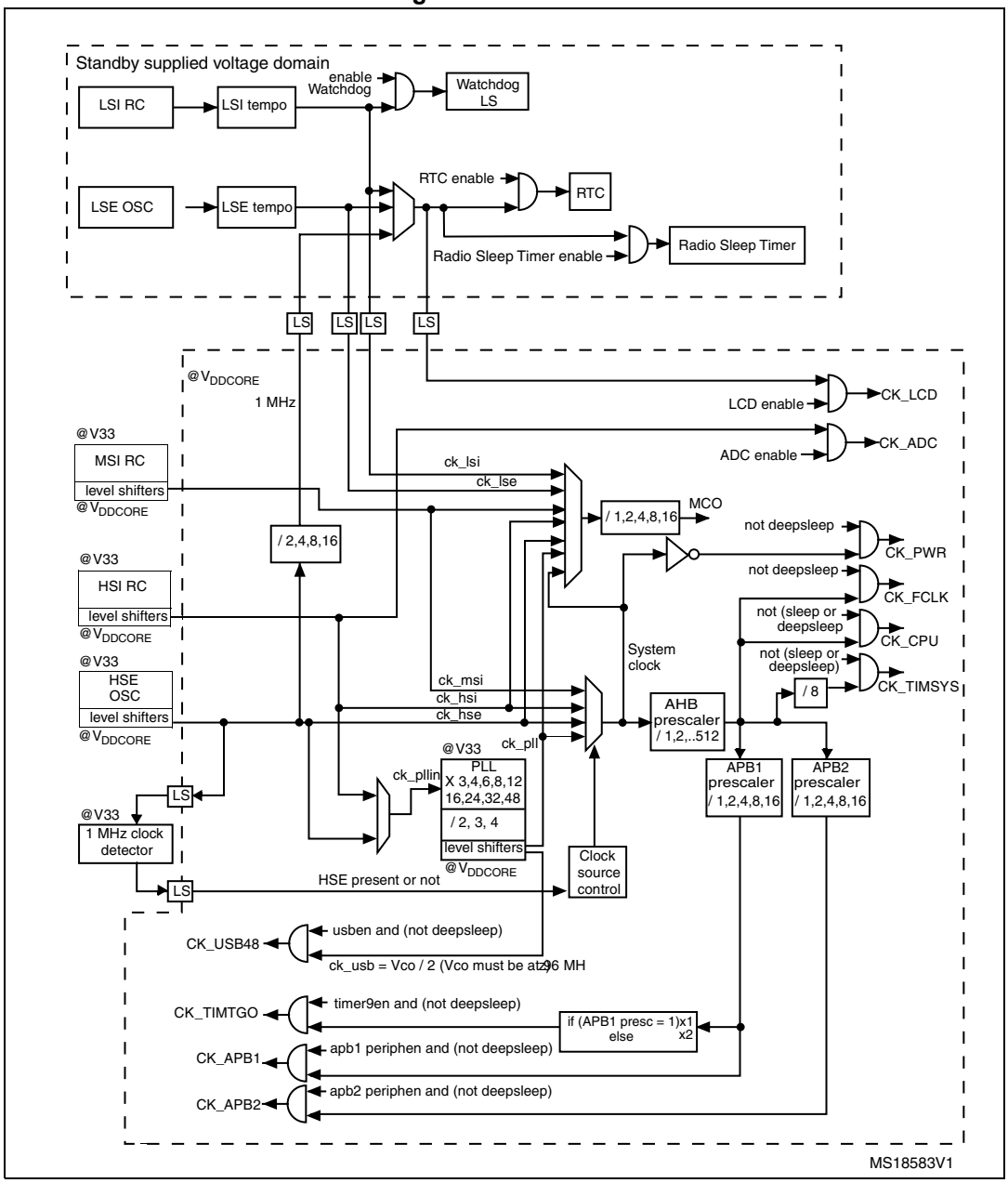
3.4 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

- **Clock prescaler**: to get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.
- **Safe clock switching**: clock sources can be changed safely on the fly in run mode through a configuration register.
- **Clock management**: to reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.
- **System clock source**: three different clock sources can be used to drive the master clock SYSCLK:
  - 1-24 MHz high-speed external crystal (HSE), that can supply a PLL
  - 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLL
  - Multispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.
- **Auxiliary clock source**: two ultra-low-power clock sources that can be used to drive the LCD controller and the real-time clock:
  - 32.768 kHz low-speed external crystal (LSE)
  - 37 kHz low-speed internal RC (LSI), also used to drive the independent watchdog. The LSI clock can be measured using the high-speed internal RC oscillator for greater precision.
- **RTC and LCD clock sources:** the LSI, LSE or HSE sources can be chosen to clock the RTC and the LCD, whatever the system clock.
- **USB clock source:** the embedded PLL has a dedicated 48 MHz clock output to supply the USB interface.
- **Startup clock:** after reset, the microcontroller restarts by default with an internal 2 MHz clock (MSI). The prescaler ratio and clock source can be changed by the application program as soon as the code execution starts.
- **Clock security system (CSS):** this feature can be enabled by software. If a HSE clock failure occurs, the master clock is automatically switched to HSI and a software interrupt is generated if enabled.
- **Clock-out capability (MCO: microcontroller clock output):** it outputs one of the internal clocks for external use by the application.

Several prescalers allow the configuration of the AHB frequency, each APB (APB1 and APB2) domains. The maximum frequency of the AHB and the APB domains is 32 MHz. See *Figure 2* for details on the clock tree.

Figure 2. Clock tree



3.5 Low-power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the sub-second, second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides two programmable alarms and programmable periodic interrupts with wakeup from Stop and Standby modes.

The programmable wakeup time ranges from 120 µs to 36 hours.

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

The RTC can also be automatically corrected with a 50/60Hz stable powerline.

The RTC calendar can be updated on the fly down to sub second precision, which enables network system synchronization.

A time stamp can record an external event occurrence, and generates an interrupt.

There are thirty-two 32-bit backup registers provided to store 128 bytes of user application data. They are cleared in case of tamper detection.

Three pins can be used to detect tamper events. A change on one of these pins can reset backup register and generate an interrupt. To prevent false tamper event, like ESD event, these three tamper inputs can be digitally filtered.

3.6 GPIOs (general-purpose inputs/outputs)

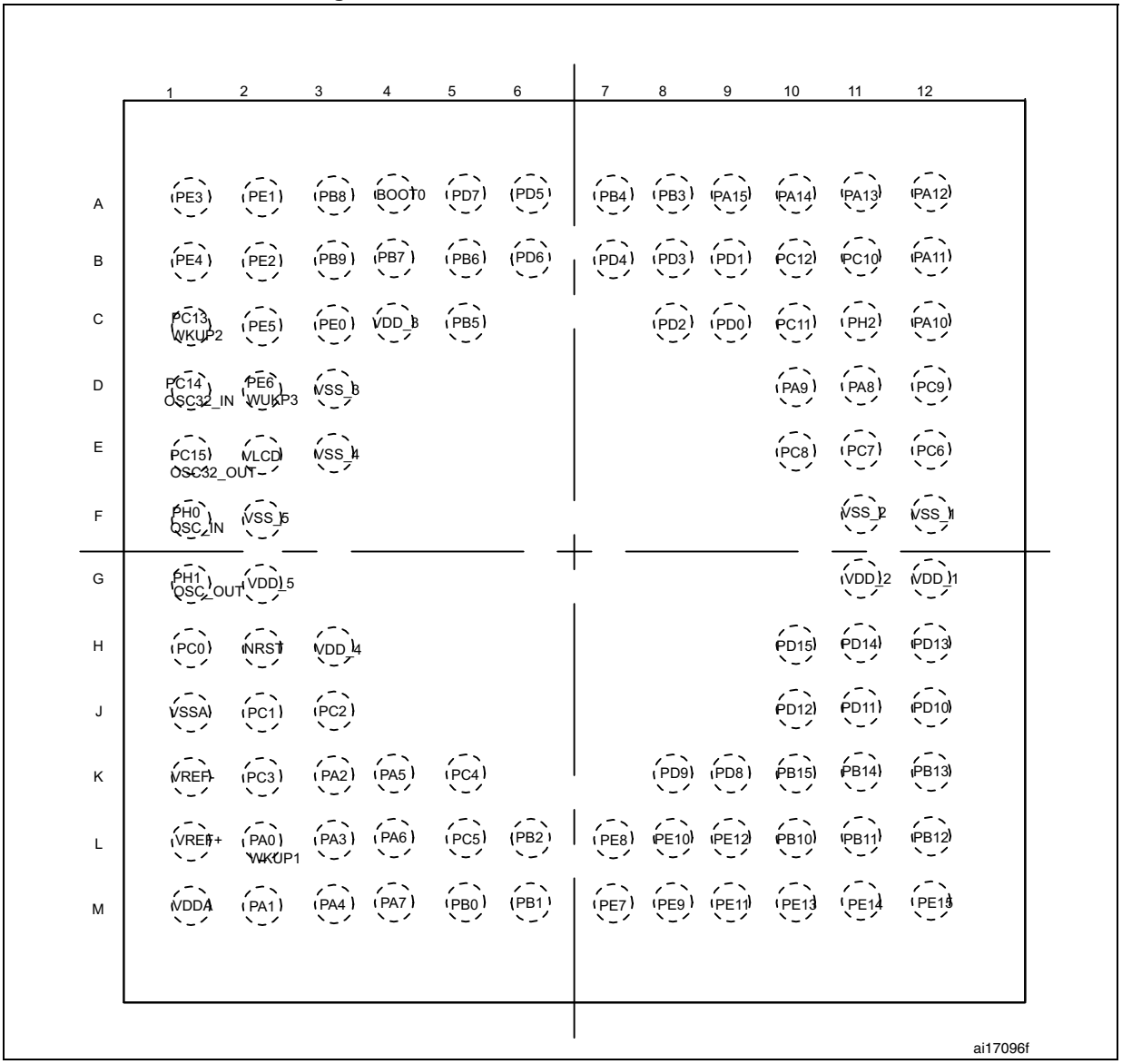
Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 24 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 83 GPIOs can be connected to the 16 external interrupt lines. The 8 other lines are connected to RTC, PVD, USB, comparator events or capacitive sensing acquisition.

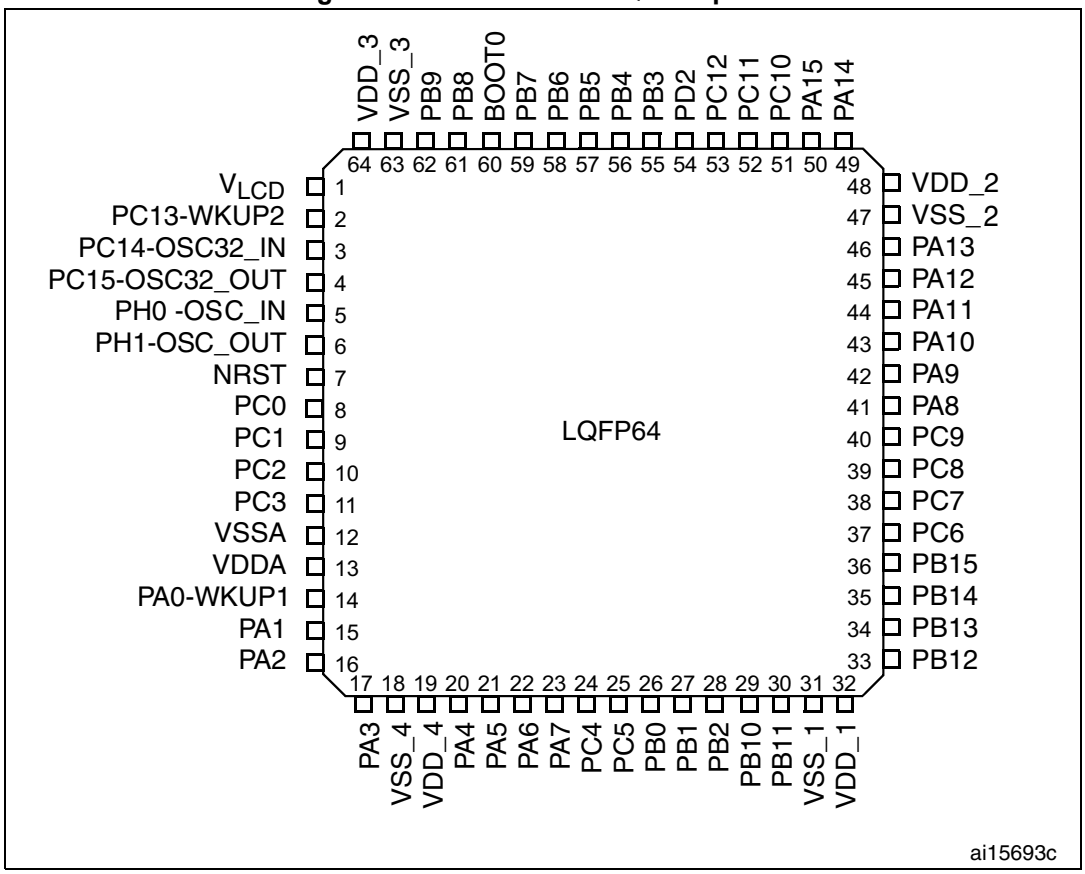
4 Pin descriptions

Figure 3. STM32L15xVC UFBGA100 ballout



1. This figure shows the package top view.

Figure 5. STM32L15xRC LQFP64 pinout



1. This figure shows the package top view.

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type(1)	I / O Structure	Main function(2) (after reset)	Pin functions	
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48					Alternate functions	Additional functions
M6	36	27	H3	19	PB1	I/O	FT	PB1	TIM3_CH4/LCD_SEG6	ADC_IN9/ COMP1_INP/ VREF_OUT
L6	37	28	G3	20	PB2	I/O	FT	PB2 /BOOT1	BOOT1	VLCDRAIL1/ ADCIN0b
M7	38	-	-	-	PE7	I/O	TC	PE7	-	ADC_IN22/ COMP1_INP
L7	39	-	-	-	PE8	I/O	TC	PE8	-	ADC_IN23/ COMP1_INP
M8	40	-	-	-	PE9	-	TC	PE9	TIM2_CH1_ETR/ TIM5_ETR	ADC_IN24/ COMP1_INP
L8	41	-	-	-	PE10	I/O	TC	PE10	TIM2_CH2	ADC_IN25/ COMP1_INP
M9	42	-	-	-	PE11	I/O	FT	PE11	TIM2_CH3	VLCDRAIL2
L9	43	-	-	-	PE12	I/O	FT	PE12	TIM2_CH4/SPI1_NSS	VLCDRAIL3
M10	44	-	-	-	PE13	I/O	FT	PE13	SPI1_SCK	-
M11	45	-	-	-	PE14	I/O	FT	PE14	SPI1_MISO	-
M12	46	-	-	-	PE15	I/O	FT	PE15	SPI1_MOSI	-
L10	47	29	J2	21	PB10	I/O	FT	PB10	TIM2_CH3/I2C2_SCL/ USART3_TX/ LCD_SEG10	-
L11	48	30	H2	22	PB11	I/O	FT	PB11	TIM2_CH4/I2C2_SDA/ USART3_RX/ LCD_SEG11	-
-	-	-	H5	-	V_{SS}	S	-	V_{SS}	-	-
F12	49	31	J1	23	V_{SS_1}	S	-	V_{SS_1}	-	-
G12	50	32	H1	24	V_{DD_1}	S	-	V_{DD_1}	-	-

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type(1)	I / O Structure	Main function(2) (after reset)	Pin functions	
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48					Alternate functions	Additional functions
L12	51	33	G2	25	PB12	I/O	FT	PB12	TIM10_CH1 /I2C2_SMBA/ SPI2_NSS/I2S2_WS/ USART3_CK/ LCD_SEG12	ADC_IN18/ COMP1_INP/ VLCDRAIL2
K12	52	34	G1	26	PB13	I/O	FT	PB13	TIM9_CH1/SPI2_SCK/ I2S2_CK/ USART3_CTS/ LCD_SEG13	ADC_IN19/ COMP1_INP
K11	53	35	F3	27	PB14	I/O	FT	PB14	TIM9_CH2/SPI2_MISO/ USART3_RTS/ LCD_SEG14	ADC_IN20/ COMP1_INP
K10	54	36	F2	28	PB15	I/O	FT	PB15	TIM11_CH1/SPI2_MOSI /I2S2_SD/LCD_SEG15	ADC_IN21/ COMP1_INP/ RTC_REFIN
K9	55	-	-	-	PD8	I/O	FT	PD8	USART3_TX/ LCD_SEG28	-
K8	56	-	-	-	PD9	I/O	FT	PD9	USART3_RX/ LCD_SEG29	-
J12	57	-	-	-	PD10	I/O	FT	PD10	USART3_CK/ LCD_SEG30	-
J11	58	-	-	-	PD11	I/O	FT	PD11	USART3_CTS/ LCD_SEG31	-
J10	59	-	-	-	PD12	I/O	FT	PD12	TIM4_CH1/ USART3_RTS/ LCD_SEG32	-
H12	60	-	-	-	PD13	I/O	FT	PD13	TIM4_CH2/LCD_SEG33	-
H11	61	-	-	-	PD14	I/O	FT	PD14	TIM4_CH3/LCD_SEG34	-
H10	62	-	-	-	PD15	I/O	FT	PD15	TIM4_CH4/LCD_SEG35	-
E12	63	37	F1	-	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/ LCD_SEG24	-

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type(1)	I / O Structure	Main function(2) (after reset)	Pin functions	
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48					Alternate functions	Additional functions
C10	79	52	A3	-	PC11	I/O	FT	PC11	SPI3_MISO/ USART3_RX/ LCD_SEG29/ LCD_SEG41/ LCD_COM5	-
B10	80	53	B4	-	PC12	I/O	FT	PC12	SPI3_MOSI/I2S3_SD/ USART3_CK/ LCD_SEG30/ LCD_SEG42/ LCD_COM6	-
C9	81	-	-	-	PD0	I/O	FT	PD0	TIM9_CH1/SPI2_NSS/ I2S2_WS	-
B9	82	-	-	-	PD1	I/O	FT	PD1	SPI2_SCK/I2S2_CK	-
C8	83	54	A4	-	PD2	I/O	FT	PD2	TIM3_ETR/LCD_SEG31 /LCD_SEG43/ LCD_COM7	-
B8	84	-	-	-	PD3	I/O	FT	PD3	SPI2_MISO/ USART2_CTS	-
B7	85	-	-	-	PD4	I/O	FT	PD4	SPI2_MOSI/I2S2_SD/ USART2_RTS	-
A6	86	-		-	PD5	I/O	FT	PD5	USART2_TX	-
B6	87	-	-	-	PD6	I/O	FT	PD6	USART2_RX	-
A5	88	-	-	-	PD7	I/O	FT	PD7	TIM9_CH2/USART2_CK	-
A8	89	55	C4	39	PB3	I/O	FT	JTDO	TIM2_CH2/SPI1_SCK/ SPI3_SCK/I2S3_CK/ LCD_SEG7/JTDO	COMP2_INM
A7	90	56	D4	40	PB4	I/O	FT	NJTRST	TIM3_CH1/SPI1_MISO/ SPI3_MISO/LCD_SEG8 /NJTRST	COMP2_INP
C5	91	57	A5	41	PB5	I/O	FT	PB5	TIM3_CH2/I2C1_SMBA/ SPI1_MOSI/SPI3_MOSI /I2S3_SD/LCD_SEG9	COMP2_INP

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number												
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO11	. .	AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
PE8	-	-	-	-	-	-	-	-		-		TIMx_IC1	EVENT OUT
PE9	-	TIM2_CH1_ETR	TIM5_ETR	-	-	-	-	-		-		TIMx_IC2	EVENT OUT
PE10	-	TIM2_CH2	-	-	-	-	-	-		-		TIMx_IC3	EVENT OUT
PE11	-	TIM2_CH3	-	-	-	-	-	-		-		TIMx_IC4	EVENT OUT
PE12	-	TIM2_CH4	-	-	-	SPI1_NSS	-	-		-		TIMx_IC1	EVENT OUT
PE13	-	-	-	-	-	SPI1_SCK	-	-		-		TIMx_IC2	EVENT OUT
PE14	-	-	-	-	-	SPI1_MISO	-	-		-		TIMx_IC3	EVENT OUT
PE15	-	-	-	-	-	SPI1_MOSI	-	-		-		TIMx_IC4	EVENT OUT
PH0OSC _IN	-	-	-	-	-	-	-	-		-		-	-
PH1OSC_ OUT	-	-	-	-	-	-	-	-		-		-	-
PH2	-	-	-	-	-	-	-	-		-		-	-

Table 14. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Max	Unit
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation(5)	–40	85	°C
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	110	

1. When the ADC is used, refer to *Table 56: ADC characteristics*.
2. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and up to 140 mV in operation.
3. To sustain a voltage higher than VDD+0.3V, the internal pull-up/pull-down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_J max (see *Table 73: Thermal characteristics on page 128*).
5. In low-power dissipation state, T_A can be extended to -40°C to 105°C temperature range as long as T_J does not exceed T_J max (see *Table 73: Thermal characteristics on page 128*).

6.3.2 Embedded reset and power control block characteristics

The parameters given in the following table are derived from the tests performed under the conditions summarized in *Table 14*.

Table 15. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}(1)	V_{DD} rise time rate	BOR detector enabled	0	-	∞	µs/V
		BOR detector disabled	0	-	1000	
	V_{DD} fall time rate	BOR detector enabled	20	-	∞	
		BOR detector disabled	0	-	1000	
$T_{RSTTEMPO}$(1)	Reset temporization	V_{DD} rising, BOR enabled	-	2	3.3	ms
		V_{DD} rising, BOR disabled(2)	0.4	0.7	1.6	
$V_{POR/PDR}$	Power on/power down reset threshold	Falling edge	1	1.5	1.65	V
		Rising edge	1.3	1.5	1.65	
V_{BOR0}	Brown-out reset threshold 0	Falling edge	1.67	1.7	1.74	
		Rising edge	1.69	1.76	1.8	
V_{BOR1}	Brown-out reset threshold 1	Falling edge	1.87	1.93	1.97	
		Rising edge	1.96	2.03	2.07	
V_{BOR2}	Brown-out reset threshold 2	Falling edge	2.22	2.30	2.35	
		Rising edge	2.31	2.41	2.44	

Table 19. Current consumption in Run mode, code with data processing running from RAM

Symbol	Parameter	Conditions		f_{HCLK}	Typ	Max(1)	Unit
I_{DD} (Run from RAM)	Supply current in Run mode, code executed from RAM, Flash switched off	$f_{HSE} = f_{HCLK}$ up to 16 MHz, included $f_{HSE} = f_{HCLK}/2$ above 16 MHz (PLL ON)(2)	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	1 MHz	185	240	µA
				2 MHz	345	410	
				4 MHz	645	880(3)	
			Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	4 MHz	0.755	1.4	mA
				8 MHz	1.5	2.1	
				16 MHz	3	3.5	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	8 MHz	1.8	2.8	
				16 MHz	3.6	4.1	
				32 MHz	7.15	8.3	
		HSI clock source (16 MHz)	Range 2, V_{CORE}=1.5 V VOS[1:0] = 10	16 MHz	2.95	3.5	
			Range 1, V_{CORE}=1.8 V VOS[1:0] = 01	32 MHz	7.15	8.4	
		MSI clock, 65 kHz	Range 3, V_{CORE}=1.2 V VOS[1:0] = 11	65 kHz	38.5	85	µA
		MSI clock, 524 kHz		524 kHz	110	160	
		MSI clock, 4.2 MHz		4.2 MHz	690	810	

1. Guaranteed by characterization results, unless otherwise specified.
2. Oscillator bypassed (HSEBYP = 1 in RCC_CR register).
3. Guaranteed by test in production.

Table 23. Typical and maximum current consumptions in Stop mode (continued)

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Stop)	Supply current in Stop mode (RTC disabled)	Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled	T_A = -40°C to 25°C	1.8	2.2	µA
		Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)	T_A = -40°C to 25°C	0.435	1	
			T_A = 55°C	0.99	3	
			T_A= 85°C	2.4	9	
			T_A = 105°C	5.5	22(5)	
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	MSI = 4.2 MHz	T_A = -40°C to 25°C	2	-	mA
		MSI = 1.05 MHz		1.45	-	
		MSI = 65 kHz(6)		1.45	-	

1. Guaranteed by characterization results, unless otherwise specified.
2. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.
3. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
4. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
5. Guaranteed by test in production.
6. When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining part of the wakeup period, the current corresponds the Run mode current.

Table 29. HSE oscillator characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC_IN}	Oscillator frequency	-	1		24	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
C	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(3)	R_S = 30 Ω	-	20	-	pF
I_{HSE}	HSE driving current	V_{DD}= 3.3 V, V_{IN} = V_{SS} with 30 pF load	-	-	3	mA
$I_{DD(HSE)}$	HSE oscillator power consumption	C = 20 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.7 (stabilized)	mA
		C = 10 pF f_{OSC} = 16 MHz	-	-	2.5 (startup) 0.46 (stabilized)	
g_m	Oscillator transconductance	Startup	3.5	-	-	mA /V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	1	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by characterization results.
3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}. Refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website *www.st.com*.

Table 33. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Typ	Max	Unit
$t_{STAB(MSI)}$(2)	MSI oscillator stabilization time	MSI range 0	-	40	µs
		MSI range 1	-	20	
		MSI range 2	-	10	
		MSI range 3	-	4	
		MSI range 4	-	2.5	
		MSI range 5	-	2	
		MSI range 6, Voltage range 1 and 2	-	2	
		MSI range 3, Voltage range 3	-	3	
$f_{OVER(MSI)}$	MSI oscillator frequency overshoot	Any range to range 5	-	4	MHz
		Any range to range 6	-	6	

1. This is a deviation for an individual part, once the initial frequency has been measured.
2. Guaranteed by characterization results.

Output driving current

The GPIOs (general purpose input/outputs) can sink or source up to ±8 mA, and sink or source up to ±20 mA with the non-standard V_{OL}/V_{OH} specifications given in *Table 44*.

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in *Section 6.2*:

- The sum of the currents sourced by all the I/Os on $V_{DD,}$ plus the maximum Run consumption of the MCU sourced on $V_{DD,}$ cannot exceed the absolute maximum rating $I_{VDD(\Sigma)}$ (see *Table 12*).
- The sum of the currents sunk by all the I/Os on V_{SS} plus the maximum Run consumption of the MCU sunk on V_{SS} cannot exceed the absolute maximum rating $I_{VSS(\Sigma)}$ (see *Table 12*).

Output voltage levels

Unless otherwise specified, the parameters given in *Table 44* are derived from tests performed under the conditions summarized in *Table 14*. All I/Os are CMOS and TTL compliant.

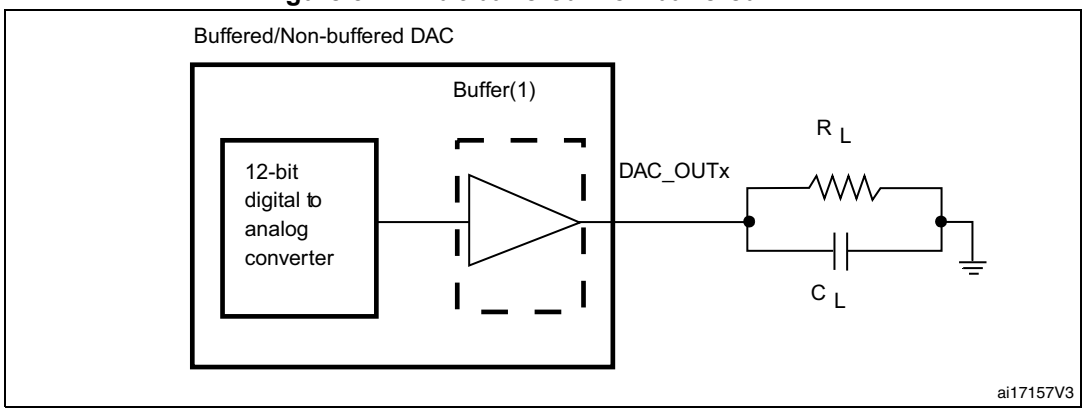
Table 44. Output voltage characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL} (1)(2)	Output low level voltage for an I/O pin	I_{IO} = 8 mA 2.7 V < V_{DD} < 3.6 V	-	0.4	V
V_{OH} (2)(3)	Output high level voltage for an I/O pin		V_{DD}-0.4	-	
V_{OL} (3)(4)	Output low level voltage for an I/O pin	I_{IO} = 4 mA 1.65 V < V_{DD} < 3.6 V	-	0.45	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}-0.45	-	
V_{OL} (1)(4)	Output low level voltage for an I/O pin	I_{IO} = 20 mA 2.7 V < V_{DD} < 3.6 V	-	1.3	
V_{OH} (3)(4)	Output high level voltage for an I/O pin		V_{DD}-1.3	-	

1. The I_{IO} current sunk by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. Guaranteed by test in production.
3. The I_{IO} current sourced by the device must always respect the absolute maximum rating specified in *Table 12* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD}.
4. Guaranteed by characterization results.

4. Difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 4095.
5. Difference between the value measured at Code (0x800) and the ideal value = V_{REF+}/2.
6. Difference between the value measured at Code (0x001) and the ideal value.
7. Difference between ideal slope of the transfer function and measured slope computed from code 0x000 and 0xFFF when buffer is OFF, and from code giving 0.2 V and (V_{DDA} – 0.2) V when buffer is ON.
8. In buffered mode, the output can overshoot above the final value for low input code (starting from min value).

Figure 31. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

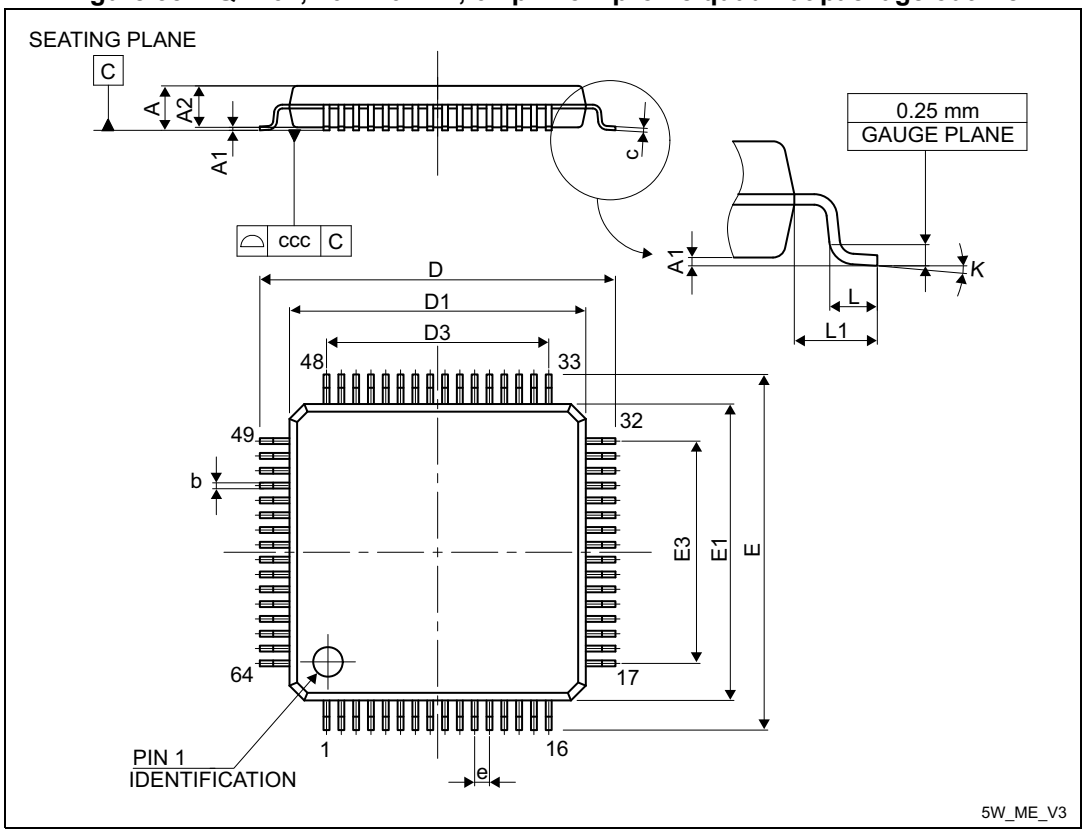
6.3.19 Operational amplifier characteristics

Table 60. Operational amplifier characteristics

Symbol	Parameter		Condition(1)	Min(2)	Typ	Max(2)	Unit
CMIR	Common mode input range		-	0	-	V_{DD}	
VI_{OFFSET}	Input offset voltage	Maximum calibration range	-	-	-	±15	mV
		After offset calibration	-	-	-	±1.5	
ΔVI_{OFFSET}	Input offset voltage drift	Normal mode	-	-	-	±40	µV/°C
		Low-power mode	-	-	-	±80	
I_{IB}	Input current bias	Dedicated input	75 °C	-	-	1	nA
		General purpose input		-	-	10	
I_{LOAD}	Drive current	Normal mode	-	-	-	500	µA
		Low-power mode	-	-	-	100	
I_{DD}	Consumption	Normal mode	No load, quiescent mode	-	100	220	µA
		Low-power mode		-	30	60	
CMRR	Common mode rejection ration	Normal mode	-	-	-85	-	dB
		Low-power mode	-	-	-90	-	

7.2 LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package information

Figure 35. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package outline



1. Drawing is not to scale.

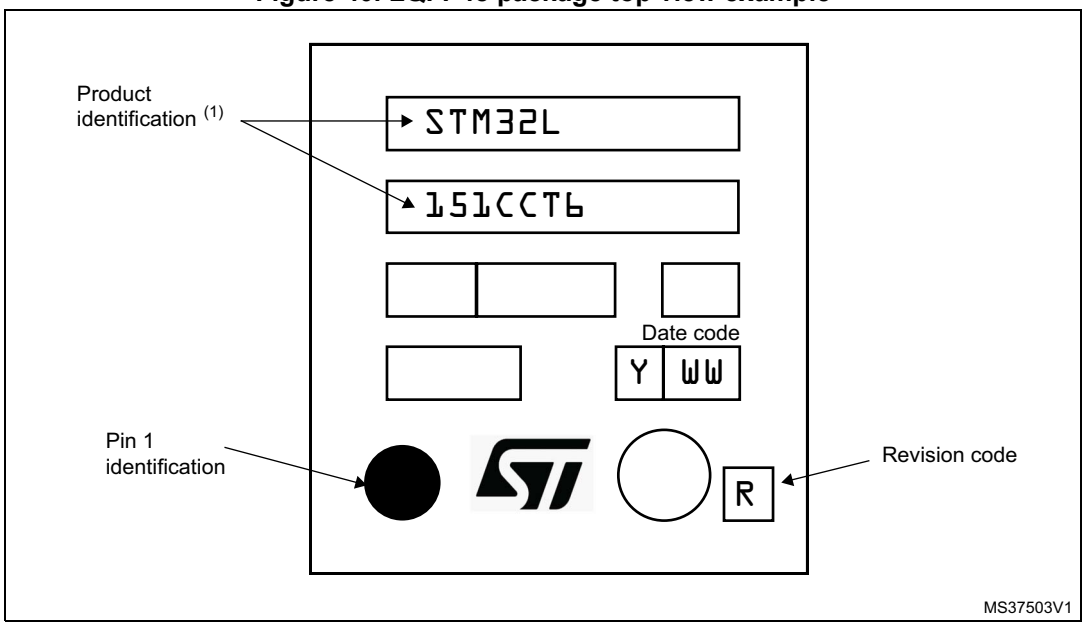
Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Figure 40. LQFP48 package top view example

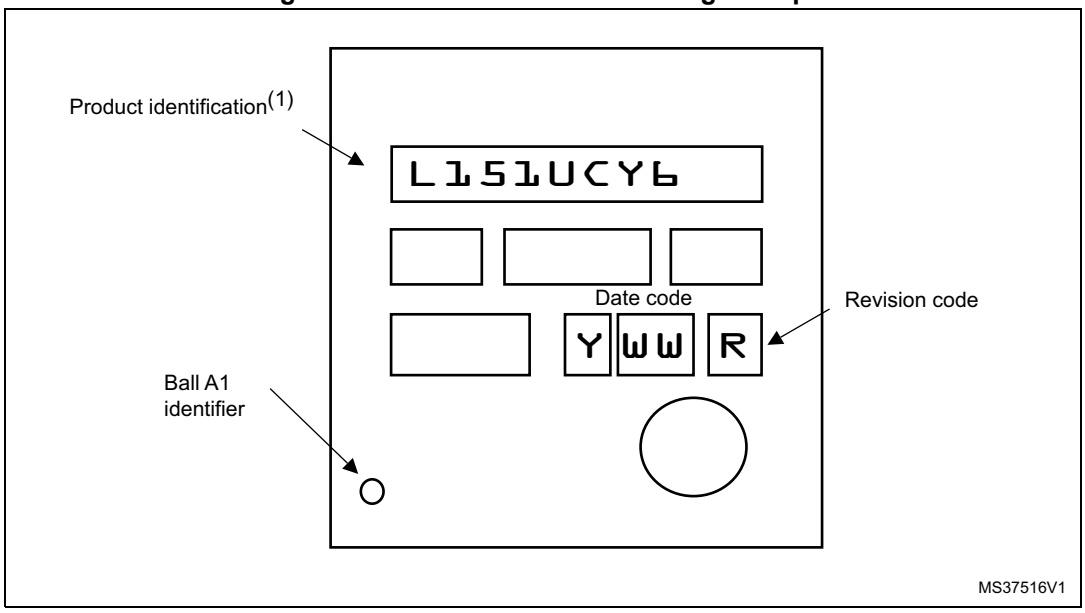


1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity

Marking of engineering samples

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 48. WLCSP63 device marking example



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity